



12TQ200/12TQ200S SCHOTTKY RECTIFIER

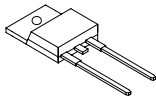

Applications:

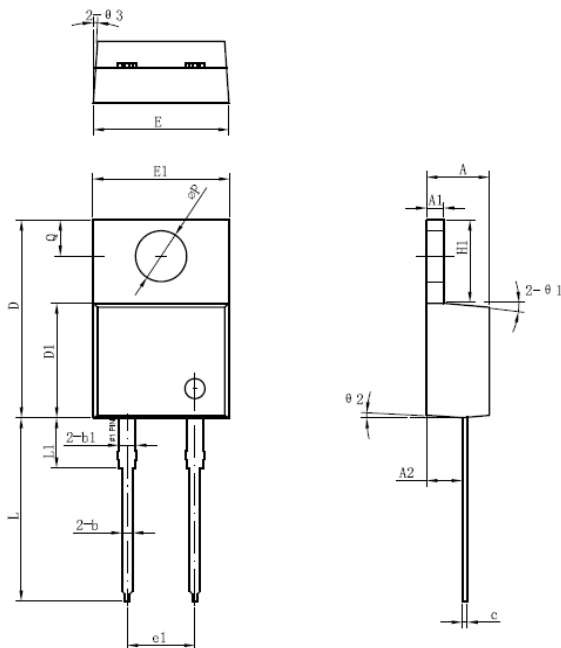
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 175°C T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

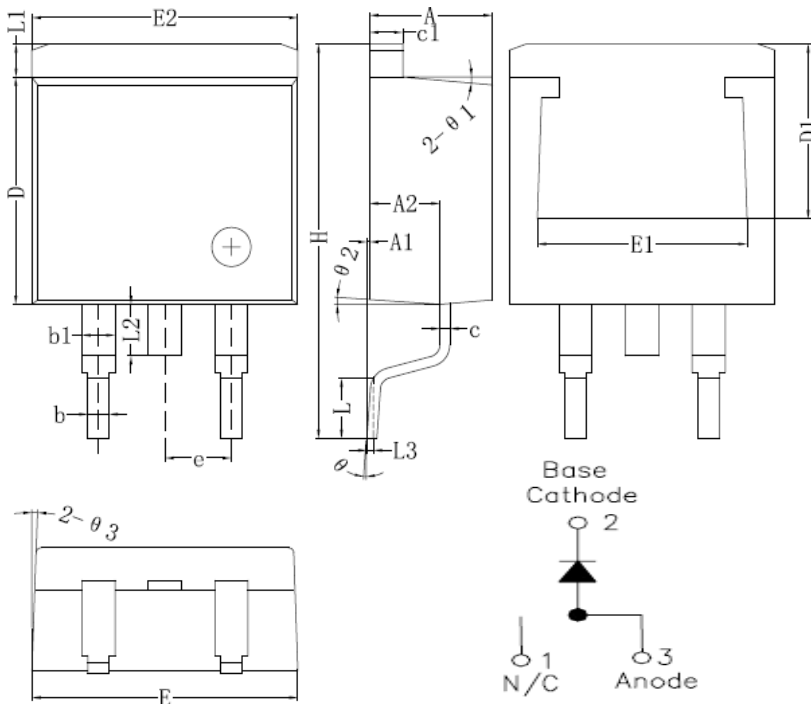
Mechanical Dimensions: In mm / Inches

Case styles	
<p>12TQ...</p>  <p>TO-220AC</p>	<p>12TQ...S</p>  <p>D²PAK</p>



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.64	14.94	15.24
D1	8.55	8.07	8.85
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1		5.08	
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1		3.80	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Ø1		5°	
Ø2		4°	
Ø3		4°	

TO-220AC

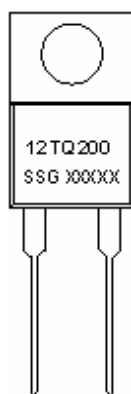


Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

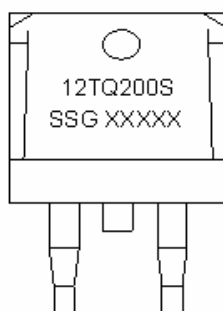
D²PAK

Technical Data
Data Sheet N0664, Rev. -
Marking Diagram:

Green Products



12TQ200



12TQ200S

Where XXXXX is YYWWL

12TQ200 =Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
12TQ...	TO-220AC (Pb-Free)	50pcs / tube
12TQ...S	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=136^{\circ}C$, rectangular wave form	15	A
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	276	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.92	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.76	V
Max. Reverse Current at DC condition	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.55	mA
Max. Reverse Current	I _{R2}	@V _R = rated V _R T _J = 125 °C	7	mA
Max. Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	300	pF
Typical Series Inductance	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change(Rated V _R)	dv/dt	-	10,000	V/μs

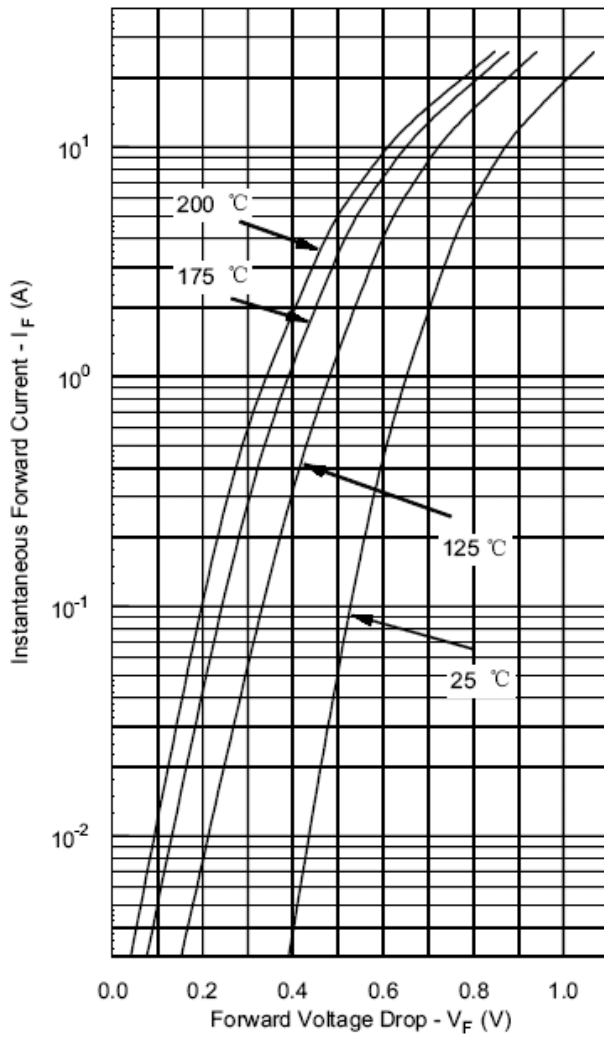
* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

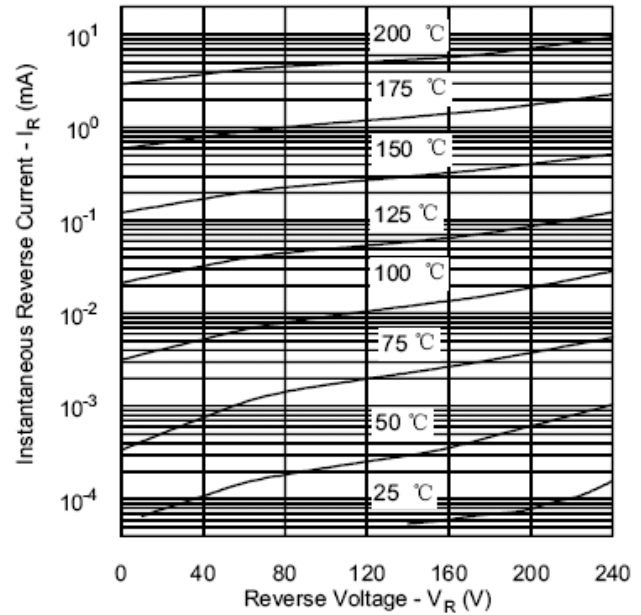
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T _J	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	2.0	°C/W
Typical Thermal Resistance, case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased	0.50	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AC, D ² PAK(Suffix "s" for D ² PAK; "MBRB" for D ² PAK)			



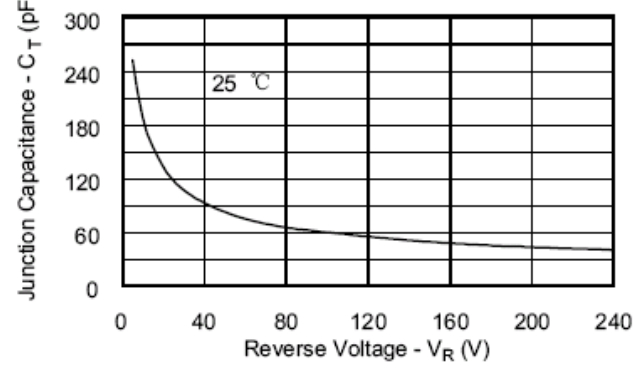
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance





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